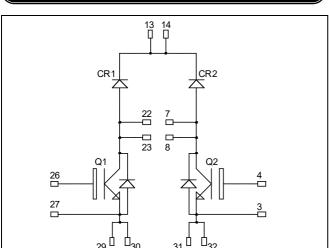
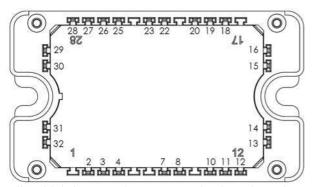


Dual Boost chopper Trench + Field Stop IGBT4 Power module



□ 16

R1



All multiple inputs and outputs must be shorted together Example: 13/14; 29/30; 22/23 ...

$V_{CES} = 1200V$ $I_{C} = 60A$ @ $T_{C} = 80^{\circ}C$

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT 4
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive TC of VCEsat
- Each leg can be easily paralleled to achieve a single boost of twice the current capability
- RoHS c-ompliant

All ratings (a) $T_j = 25$ °C unless otherwise specified

Absolute maximum ratings (per IGBT)

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Voltage		1200	V
Ţ	Continuous Collector Coment	$T_C = 25^{\circ}C$	80	
$I_{\rm C}$	Continuous Collector Current	$T_C = 80^{\circ}C$	60	Α
I_{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Power Dissipation	$T_C = 25^{\circ}C$	280	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150$ °C	100A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.



Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$, $V_{CE} =$			250	μΑ	
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.85	2.25	V
V _{CE(sat)}		$I_C = 50A$	$T_j = 150$ °C		2.25		v
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1.6 \text{mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$ $V_{GE} = \pm 15V ; V_{CE} = 600V$ $I_{C} = 50A$			2770		pF
C_{oes}	Output Capacitance				205		
C_{res}	Reverse Transfer Capacitance				160		
Q_{G}	Gate charge				0.38		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switch	ning (25°C)		130		ns
T_{r}	Rise Time	$V_{GE} = \pm 15V$			20		
$T_{d(off)} \\$	Turn-off Delay Time	$V_{CE} = 600V$ $I_{C} = 50A$			300		
T_{f}	Fall Time	$R_G = 8.2\Omega$			45		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)			150		
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$ $V_{CE} = 600V$			35		ns
$T_{d(off)}$	Turn-off Delay Time	$I_C = 50A$			350		
T_{f}	Fall Time	$R_G = 8.2\Omega$			80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25$ °C		3.8		mJ
Lon	Turn-on Switching Energy	$V_{CE} = 600V$ $T_{J} = 150^{\circ}C$			5.5		1113
$E_{\rm off}$	Turn-off Switching Energy	$I_C = 50A$	$T_J = 25$ °C		2.5		mJ
2011	Tam on a mening Energy	$R_G = 8.2\Omega$	$T_J = 150$ °C		4.5		1110
I_{sc}	Short Circuit data	$\begin{aligned} V_{GE} \leq &15 V \; ; \; V_{Bus} = 900 V \\ t_p \leq &10 \mu s \; ; \; T_j = 150 ^{\circ} C \end{aligned}$			200		A
R_{thJC}	Junction to Case Thermal Resistance					0.53	°C/W

Chopper diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					1200	V
I_{RM}	Reverse Leakage Current	$V_R = 1200V$				100	μA
I_F	DC Forward Current		$Tc = 80^{\circ}C$		60		A
		$I_F = 60A$	$I_F = 60A$		2.5	3	
V_{F}	Diode Forward Voltage	$I_F = 120A$			3		V
		$I_F = 60A$	$T_j = 125$ °C		1.8		
_	Reverse Recovery Time	$I_F = 60A$ $V_R = 800V$	$T_j = 25$ °C		265		
t_{rr}			$T_j = 125$ °C		350		ns
Qrr	Reverse Recovery Charge	$\frac{1}{\text{di/dt}} = 200 \text{A/}\mu\text{s}$	$T_j = 25$ °C		560		
			$T_j = 125$ °C		2890		nC
R_{thJC}	Junction to Case Thermal Resistance					0.9	°C/W



Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000		V
$T_{\rm J}$	Operating junction temperature range			-40	175	
T_{JOP}	Recommended junction temperature under switching conditions			-40	T _J max -25	°C
T_{STG}	Storage Temperature Range			-40	125	
$T_{\rm C}$	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

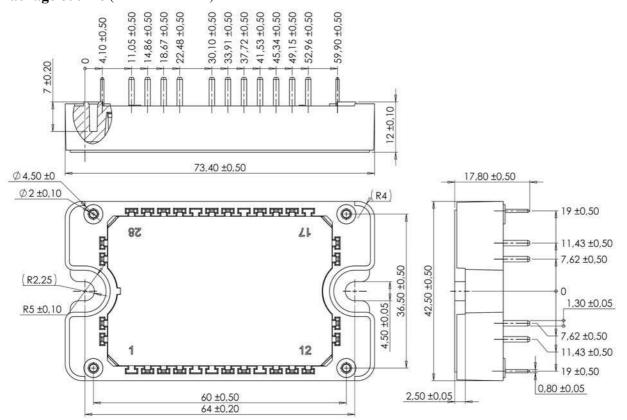
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C	25°C		50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B _{25/85}	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta \mathrm{B/B}$		T _C =100°C		4		%

$$R_{T} = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$

$$R_{T}: \text{ Thermistor value at T}$$

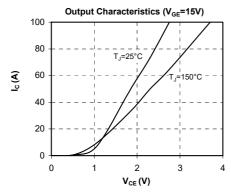
Package outline (dimensions in mm)

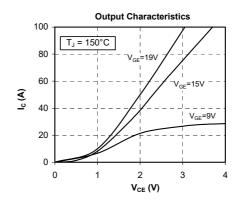


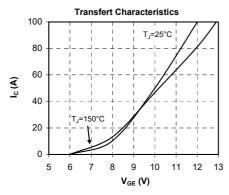
See application note 1906 - Mounting Instructions for SP3F Power Modules on $\underline{\text{www.microsemi.com}}$

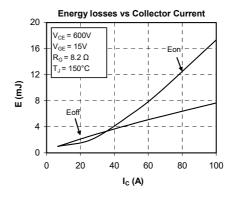


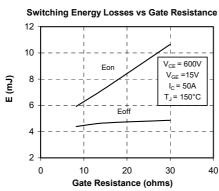
Typical Performance Curve

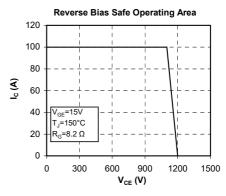


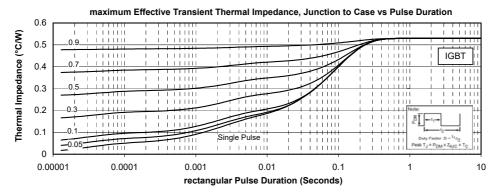








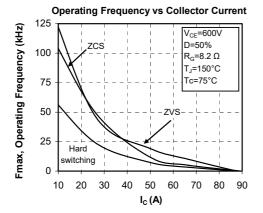


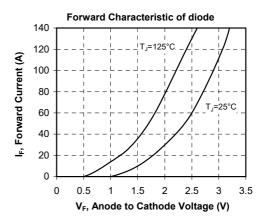


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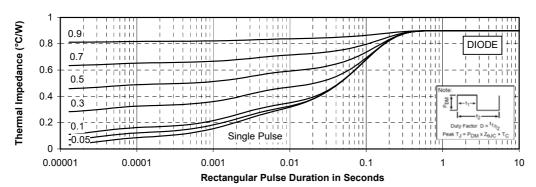


Power Matters.[™]





maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



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